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Attorney's Docket No. 5308-156

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.

Group Art Unit: 2811

Serial No.: 09/911,995

Confirmation No.: 5240

Filed: July 24, 2001

Examiner: Munson, G.

For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD  
EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND  
METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE  
SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A  
SHORTING CHANNEL

Date: February 5, 2003

BOX RCE

Commissioner for Patents

Washington, DC 20231

AMENDMENT

Sir:

Please amend the above-referenced application as follows.

In the Specification

On page 1, line 20, please insert the following paragraph following the Related Applications section:

Statement of Government Interest

The present invention was made, at least in part, with support from United States Office of Naval Research contract number N00014-99-C-0377. The government may have certain rights in this invention.

TECHNOLOGY CENTER 2800

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